Silicon NPN Power Transistors 2SD1180

DESCRIPTION

·With TO-126 package

·Low collector saturation voltage

APPLICATIONS

·Designed for use in audio and radio frequency power amplifiers

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

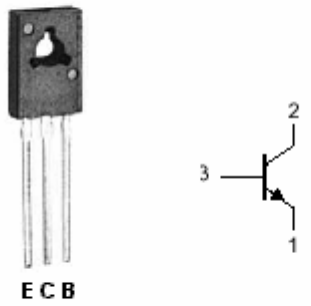

Fig.1 simplified outline (TO-126) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	120	V
V_{CEO}	Collector-emitter voltage	Open base	110	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		1.5	A
I_{CM}	Collector current-peak		2.5	A
P_C	Collector power dissipation	T_a=25□	1.2	W
		T_C=25□	20	
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

Silicon NPN Power Transistors 2SD1180

CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=10mA; I_B=0		110		V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=100μA; I_E=0		120		V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=100μA ; I_C=0		5		V
V_{CEsat}	Collector-emitter saturation voltage	I_C=1A; I_B=0.2A			0.7	V
V_{BEsat}	Base-emitter saturation voltage	I_C=1A; I_B=0.2A			1.3	V
I_{CBO}	Collector cut-off current	V_{CB}=120V; I_E=0			1.0	μA
I_{EBO}	Emitter cut-off current	V_{EB}=3V; I_C=0			1.0	μA
h_{FE}	DC current gain	I_C=150mA ; V_{CE}=5V	100			

PACKAGE OUTLINE

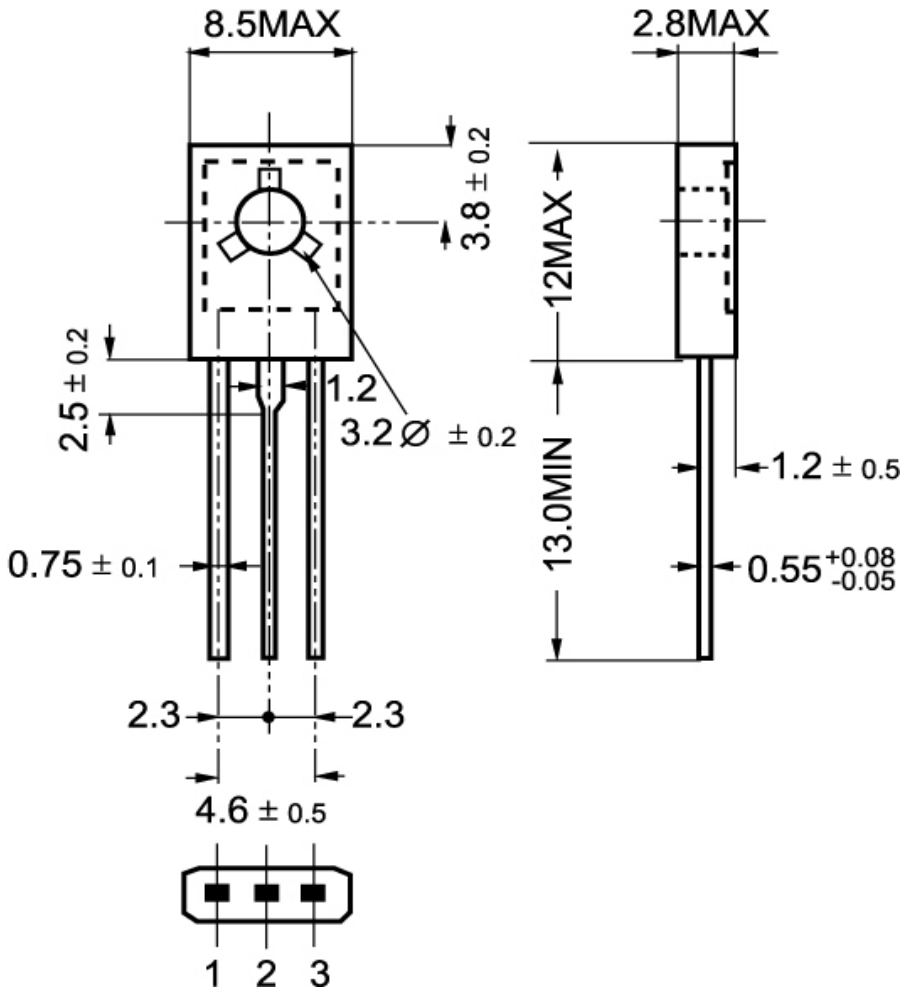

Fig.2 Outline dimensions